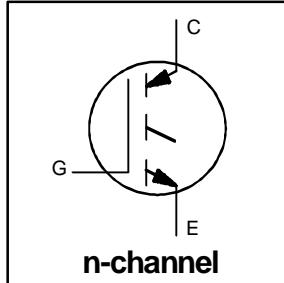


Features

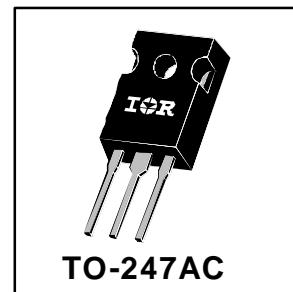
- Switching-loss rating includes all "tail" losses
- Optimized for medium operating frequency (1 to 10kHz) See Fig. 1 for Current vs. Frequency curve



$V_{CES} = 900V$
 $V_{CE(sat)} \leq 3.7V$
 @ $V_{GE} = 15V$, $I_C = 11A$

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	900	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	20	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	11	
I_{CM}	Pulsed Collector Current ①	40	
I_{LM}	Clamped Inductive Load Current ②	40	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	10	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and	-55 to $+150$	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.2	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{CES}}$	Collector-to-Emitter Breakdown Voltage	900	—	—	V	$V_{\text{GE}} = 0\text{V}, I_C = 250\mu\text{A}$
$V_{(\text{BR})\text{ECS}}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	$V_{\text{GE}} = 0\text{V}, I_C = 1.0\text{A}$
$\Delta V_{(\text{BR})\text{CES}/\Delta T_J}$	Temperature Coeff. of Breakdown Voltage	—	0.83	—	V/ $^\circ\text{C}$	$V_{\text{GE}} = 0\text{V}, I_C = 1.0\text{mA}$
$V_{\text{CE}(\text{on})}$	Collector-to-Emitter Saturation Voltage	—	2.6	3.7	V	$I_C = 11\text{A}$
		—	3.3	—		$I_C = 20\text{A}$
		—	2.9	—		$I_C = 11\text{A}, T_J = 150^\circ\text{C}$
$V_{\text{GE}(\text{th})}$	Gate Threshold Voltage	3.0	—	5.5		$V_{\text{CE}} = V_{\text{GE}}, I_C = 250\mu\text{A}$
$\Delta V_{\text{GE}(\text{th})/\Delta T_J}$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/ $^\circ\text{C}$	$V_{\text{CE}} = V_{\text{GE}}, I_C = 250\mu\text{A}$
g_{fe}	Forward Transconductance ⑤	3.6	6.9	—	S	$V_{\text{CE}} = 100\text{V}, I_C = 11\text{A}$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = 900\text{V}$
		—	—	1000		$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = 900\text{V}, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{\text{GE}} = \pm 20\text{V}$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	22	33	nC	$I_C = 11\text{A}$ $V_{\text{CC}} = 400\text{V}$ $V_{\text{GE}} = 15\text{V}$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	5.1	7.7		
Q_{gc}	Gate - Collector Charge (turn-on)	—	8.0	12		
$t_{d(\text{on})}$	Turn-On Delay Time	—	27	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 11\text{A}, V_{\text{CC}} = 720\text{V}$ $V_{\text{GE}} = 15\text{V}, R_G = 23\Omega$ Energy losses include "tail"
t_r	Rise Time	—	9.7	—		
$t_{d(\text{off})}$	Turn-Off Delay Time	—	160	280		
t_f	Fall Time	—	140	240		
E_{on}	Turn-On Switching Loss	—	0.33	—	mJ	See Fig. 9, 10, 11, 14
E_{off}	Turn-Off Switching Loss	—	0.67	—		
E_{ts}	Total Switching Loss	—	1.0	1.9		
$t_{d(\text{on})}$	Turn-On Delay Time	—	27	—	ns	$T_J = 150^\circ\text{C},$ $I_C = 11\text{A}, V_{\text{CC}} = 720\text{V}$ $V_{\text{GE}} = 15\text{V}, R_G = 23\Omega$ Energy losses include "tail"
t_r	Rise Time	—	12	—		
$t_{d(\text{off})}$	Turn-Off Delay Time	—	260	—		
t_f	Fall Time	—	250	—		
E_{ts}	Total Switching Loss	—	2.0	—	mJ	See Fig. 10, 14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	560	—	pF	$V_{\text{GE}} = 0\text{V}$ $V_{\text{CC}} = 30\text{V}$ $f = 1.0\text{MHz}$
C_{oes}	Output Capacitance	—	50	—		
C_{res}	Reverse Transfer Capacitance	—	7.3	—		

Notes:

① Repetitive rating; $V_{\text{GE}}=20\text{V}$, pulse width limited by max. junction temperature.
(See fig. 13b)

③ Repetitive rating; pulse width limited by maximum junction temperature.

⑤ Pulse width 5.0 μs , single shot.

② $V_{\text{CC}}=80\%(V_{\text{CES}})$, $V_{\text{GE}}=20\text{V}$, $L=10\mu\text{H}$, $R_G = 23\Omega$, (See fig. 13a)

④ Pulse width $\leq 80\mu\text{s}$; duty factor $\leq 0.1\%$.

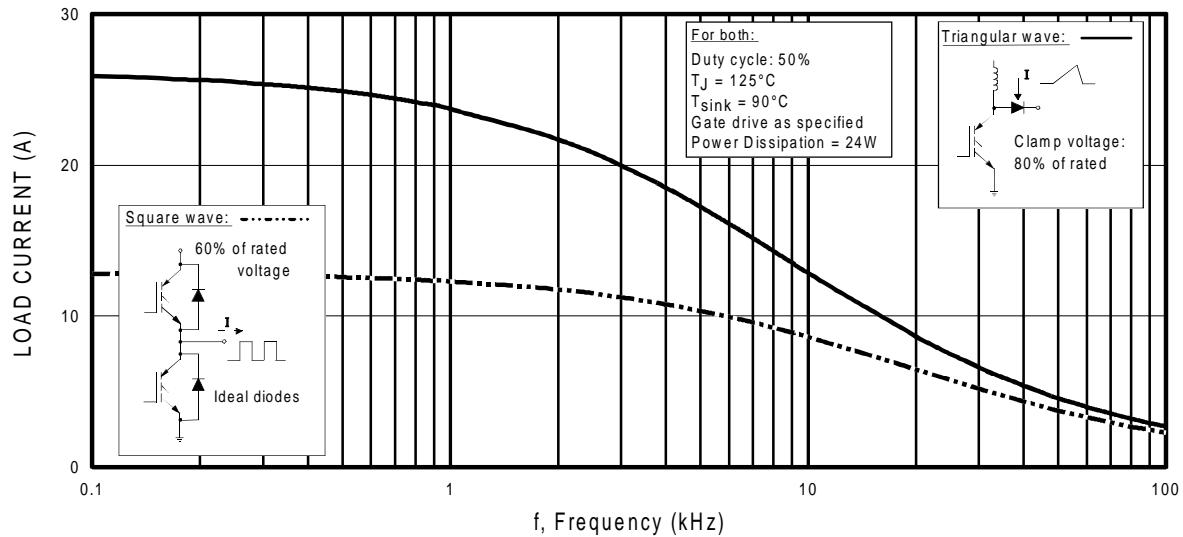


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I=I_{RMS}$ of fundamental; for triangular wave, $I=I_{PK}$)

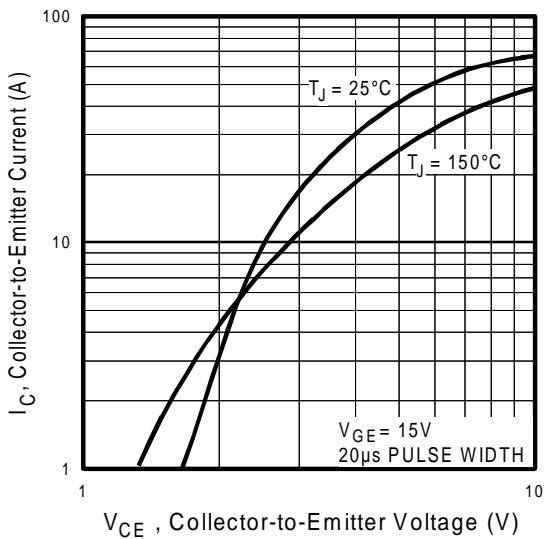


Fig. 2 - Typical Output Characteristics

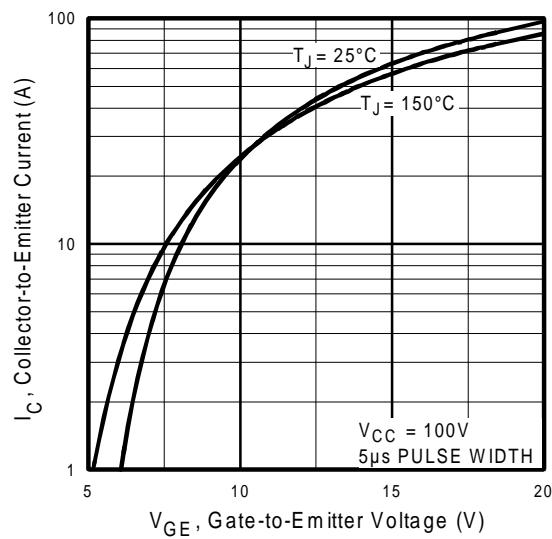


Fig. 3 - Typical Transfer Characteristics

IRGP30F

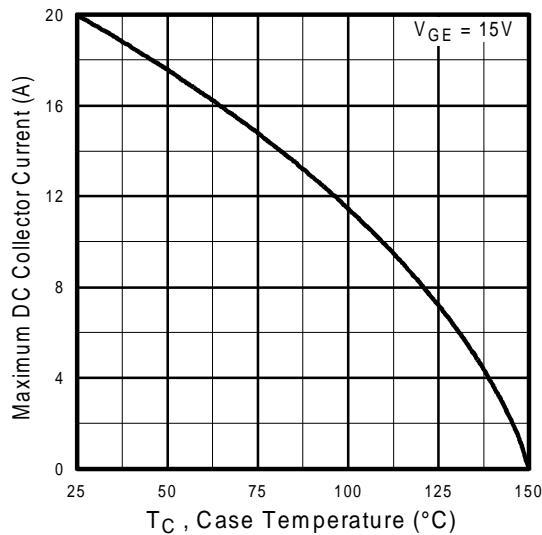


Fig. 4 - Maximum Collector Current vs. Case Temperature

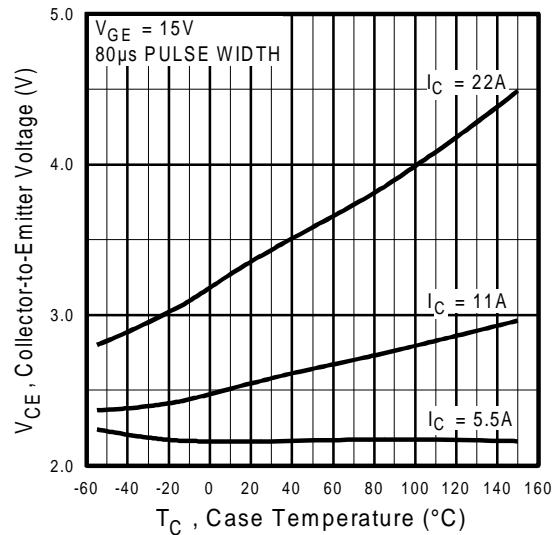


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

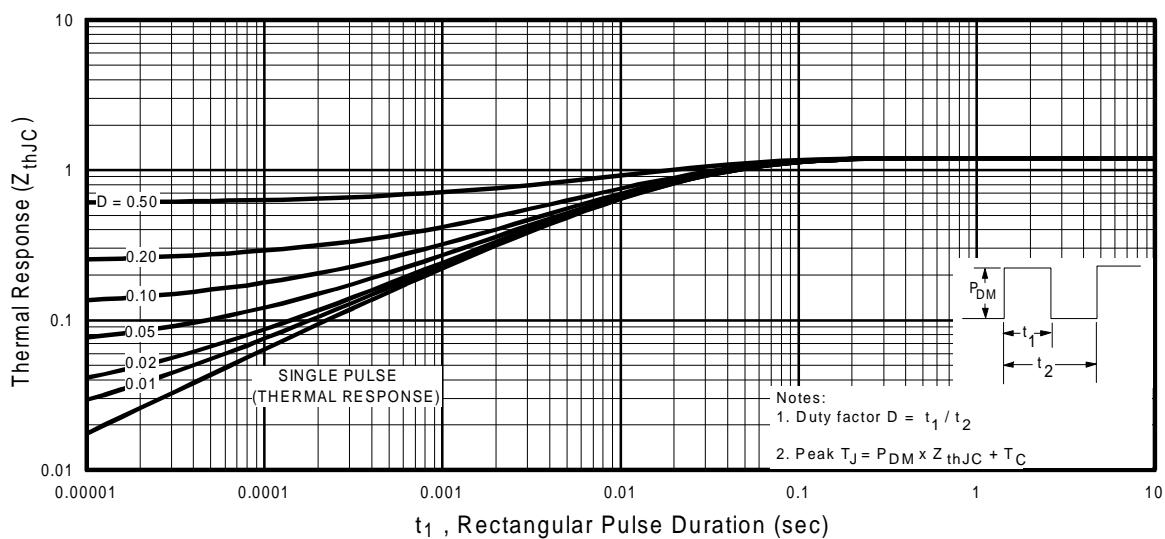


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

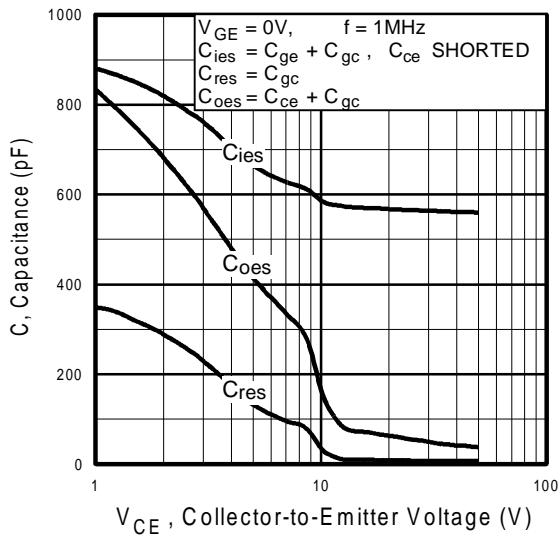


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

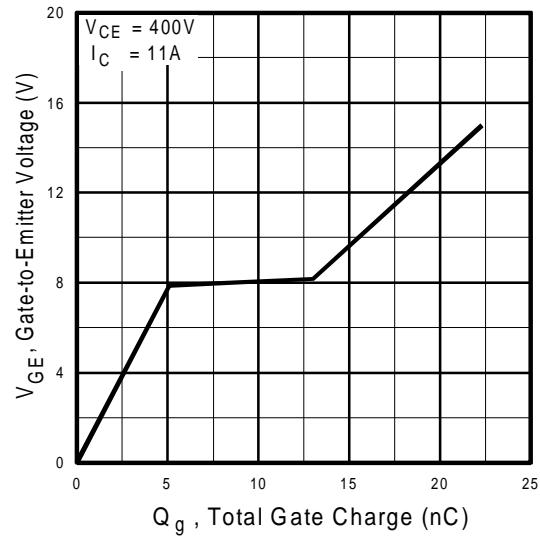


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

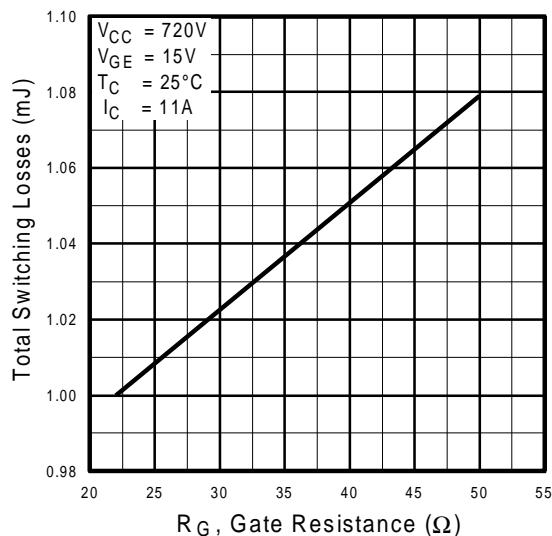


Fig. 9 - Typical Switching Losses vs. Gate Resistance

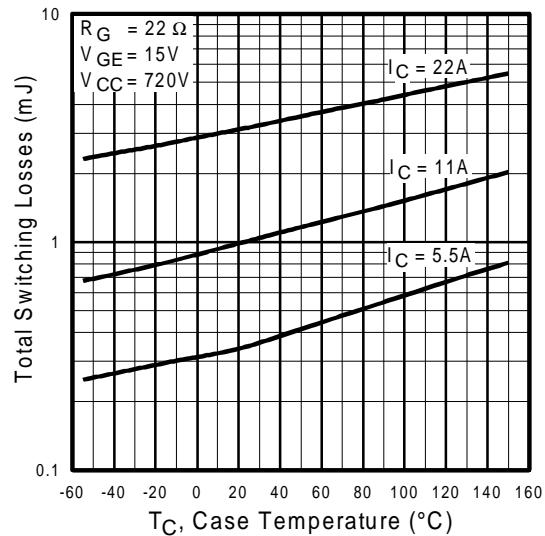


Fig. 10 - Typical Switching Losses vs. Case Temperature

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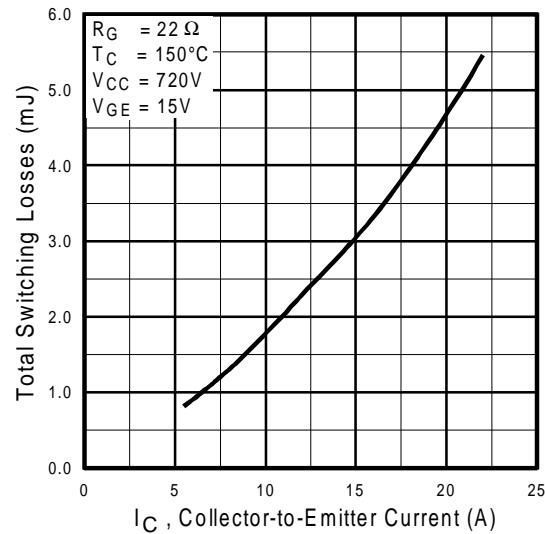


Fig. 11 - Typical Switching Losses vs.
Collector-to-Emitter Current

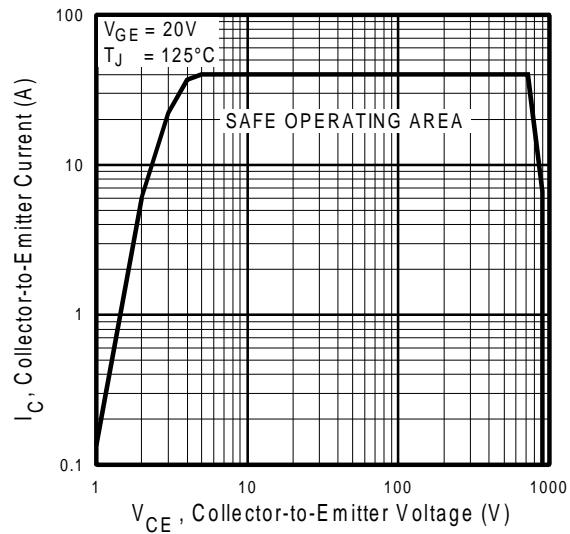


Fig. 12 - Turn-Off SOA

Refer to Section D for the following:

Appendix F: Section D - page D-8

- Fig. 13a - Clamped Inductive Load Test Circuit
- Fig. 13b - Pulsed Collector Current Test Circuit
- Fig. 14a - Switching Loss Test Circuit
- Fig. 14b - Switching Loss Waveform

Package Outline 3 - JEDEC Outline TO-247AC (TO-3P) **Section D - page D-13**